

# MG910 GaAs Hall Element

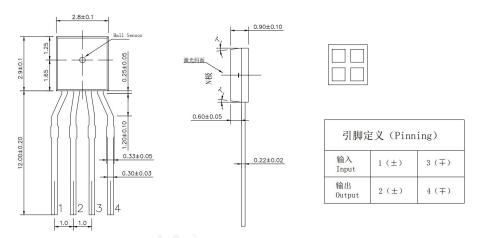
Linear GaAs Hall Element

**Excellent Thermal Characteristics** 

Thin-type SIP Package

Shipped in Bulk by Pack (500pcs devices per pack)

## Dimensional Drawing (Unit: mm)



# **Absolute Maximum Rating**

Operating Temperature Range  $-40^{\circ}\text{C} \sim 125^{\circ}\text{C}$ Storage Temperature Range  $-40^{\circ}\text{C} \sim 150^{\circ}\text{C}$ Maximum Input Current  $I_{cmax}$  13mA

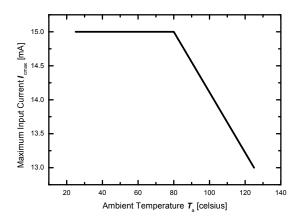


Figure 1. Maximum input current Icmax

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### Electrical Characteristics (RT=25°C)

Item Symbol Test Condi. Min. Тур. Max. Unit **B** = 50mT, **I**<sub>C</sub>=5mA Hall Voltage  $V_{\rm H}$ 36 45 54 mV  $T_a = RT$ B = 0mT,  $I_C = 0.1mA$ Input/Output Resist. 650 750 850 Ω **R**in/out  $T_a = RT$ B = 0mT,  $I_C = 5mA$ Offset Voltage -5  $V_{os}$ +5 mV  $T_a = RT$  $B = 50 \text{mT}, I_{C} = 5 \text{mA},$ Temp. Coeffi. of VH 0.06 %/°C  $|\alpha V_{H}|$ T<sub>a</sub> = 25°C ~ 125°C B = 0mT,  $I_C = 0.1mA$ , %/°C Temp. Coeffi. of Rin  $\alpha R_{in}$ 0.3  $T_a = 25^{\circ}C \sim 125^{\circ}C$ **B** = 0.1 - 0.5T, **I**<sub>C</sub> =5mA Linearity of V<sub>H</sub>  $\Delta K$ -2 +2 %  $T_a = RT$ 

Table 1. Electrical Characteristics of MG910.

Note:

1. 
$$V_{\rm H} = V_{\rm H-M} - V_{\rm os}$$

In which  $\emph{V}_{\text{H-M}}$  is the Output Hall Voltage,  $\emph{V}_{\text{H}}$  is the Hall Voltage and  $\emph{V}_{\text{os}}$  is the offset Voltage

under the identical electrical stimuli.

2. 
$$\alpha V_{\rm H} = \frac{1}{v_{\rm H} (T_{a1})} \times \frac{v_{\rm H} (T_{a2}) - v_{\rm H} (T_{a1})}{T_{a2} - T_{a1}} \times 100$$

$$T_{a1} = 25$$
°C,  $T_{a2} = 125$ °C

3. 
$$\alpha R_{\text{in}} = \frac{1}{R_{\text{in}} (T_{a1})} \times \frac{R_{\text{in}} (T_{a2}) - R_{\text{in}} (T_{a1})}{T_{a2} - T_{a1}} \times 100$$

$$T_{a1} = 25$$
°C,  $T_{a2} = 125$ °C

4. 
$$\Delta K = \frac{K(B_1) - K(B_2)}{\frac{K(B_1) + K(B_2)}{2}} \times 100$$
  $K = \frac{V_H}{I_c \times B}$ 

$$B_1 = 0.5 \text{ T}, \quad B_2 = 0.1 \text{ T}$$



## **Characteristic Curves**

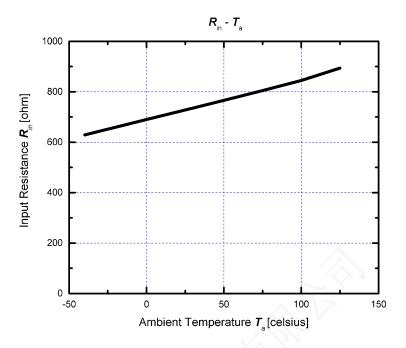


Figure 2. Input resistance  $R_{in}$  as a function of ambient temperature  $T_{a}$ 

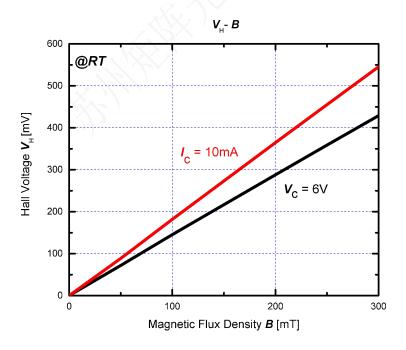


Figure 3. Hall voltage  $V_H$  as a function of magnetic flux density B

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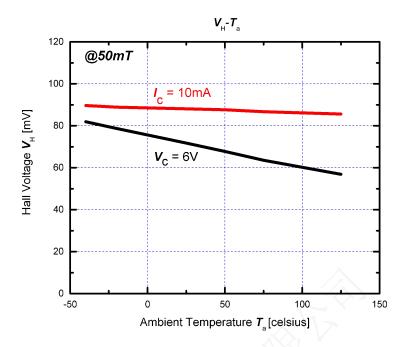


Figure 4. Hall voltage  $V_H$  as a function of ambient temperature  $T_a$ 

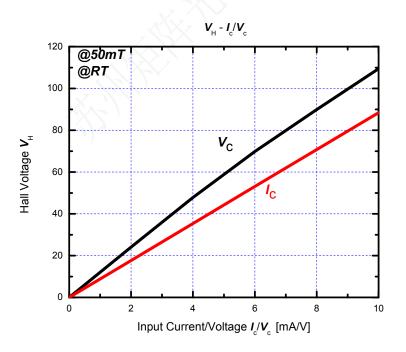


Figure 5. Hall voltage  $V_H$  as a function of electrical stimuli  $I_c/V_c$ 

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# **Reliability Test Terms**

Table 2. Reliability Test Terms, Conditions and Duration.

No.	Terms	Conditions	Duration
1	High Temperature Storage (HTS)	[JEITA EIAJ ED-4701]  Ta =150 ( 0 ~ +10 ) °C	1000 hrs
2	Heat Cycle (HC)	[JEITA EIAJ ED-4701] $T_a = -55^{\circ}\text{C} \sim 150  ^{\circ}\text{C}$ high temp normal temp low temp. $30  \text{min}  -  5  \text{min}  -  30  \text{min}$	50 cycles
3	Temp. Humidity Storage (THS)	【JEITA EIAJ ED-4701】 <b>T</b> <sub>a</sub> =85±3 °C , <b>R</b> <sub>H</sub> =85±5 %	1000 hrs
4	Resist. to Hand Soldering Heat (RHSH)	[JEITA EIAJ ED-4701]  Dipped in the 300±5 °C  solder up to the 1 mm part from the body	5 sec
5	High Temp. Operating (HTO)	$T_{\rm a}$ =125 °C , $V_{\rm c}$ =7.5V	1000 hrs

#### Criteria:

- Variation of Hall Voltage  $V_{\rm H}$  and input/output resistances  $R_{\rm in/out}$  are less than 20%.
- Variation of offset voltage  $V_{\rm os}$  is less than ±16mV.
- Other parameters in Table 1. are still within their ranges stated in Table 1.



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## **Soldering Conditions**

The following conditions should be preserved. Solder ability should be checked by yourself, because it is depend on solder paste material and other parameters.

#### Material of solder flux

- Use the resin based flux and refrain from using organic or inorganic acid based and water-soluble one.

#### Cleansing of solder flux conditions

- Use Ethanol or Isopropyl alcohol as cleansing material.
- Process temperature should be 50 °C or less.
- Duration should be 5 minutes or less.

#### Hand soldering conditions

- Apart from the mold resin more than 1mm.
- Solder at temperature 300 °C for less than 5s.

#### Wave soldering conditions

- Temperature in Pre-heating zone should be lower than 150°C.
- Temperature in Soldering zone should be lower than 280°C.

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#### **Precautions for ESD**

This product is the device that is sensitive to ESD (Electrostatic Discharge). Handling Hall Elements with the ESD-Caution mark under the environment in which

- Static electrical charge is unlikely to arise (Ex: Relative Humidity over 40%RH).
- Wearing the anti-static suit and wristband when handling the devices.
- Implementing measures against ESD as for containers that directly touch the devices.

## **Precautions for Storage**

- Products should be stored at an appropriate temperature and humidity (5°C to 35°C, 40%RH to 60%RH) after the unsealing of the MBB. Keeping products away from chlorine and corrosive gas.
- For storage longer than 2 years

Products are sealed in MBB with a desiccant. It is recommended to store in nitrogen atmosphere with MBB sealed. Oxygen and H<sub>2</sub>O of atmosphere oxidizes leads of products and lead solder ability get worse.

# **Precautions for Safety**

- Do not alter the form of this product into a gas, powder or liquid through burning, crushing or chemical processing.
- Observe laws and company regulations when discarding this product.